



Solid State Devices, Inc.

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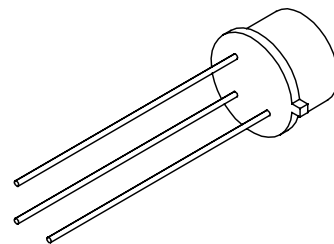
Designer's Data Sheet

FEATURES:

- Extremely Low Forward Voltage Drop
- Low Reverse Leakage
- Hermetically Sealed Package
- Guard Ring for Overvoltage Protection
- Eutectic Die Attach
- 175°C Operating Junction Temperature
- TX, TXV, or Space Level Screening Available

SSR1008/5
SSR1009/5
SSR1010/5

10 AMP
80 – 100 VOLTS
SCHOTTKY RECTIFIER



TO-5

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage and DC Blocking Voltage	V_{RRM}	80	Volts
SSR1008/5	V_{RWM}	90	
SSR1009/5	V_R	100	
SSR1010/5			
Average Rectified Output Current ^{1/} (Resistive Load, 60Hz, Sine Wave, TA=25°C)	I_O	10	Amps
Peak Surge Current ^{1/} (8.3 ms Pulse, Half Sine Wave, superimposed on I_O , allow junction to reach equilibrium between pulses, TA=25°C)	I_{FSM}	150	Amps
Operating and Storage Temperature	T_{OP} & T_{STG}	-65 to +175	°C
Maximum Thermal Resistance ^{1/} Junction to Case	$R_{\theta JC}$	7.0	°C/W

Notes: ^{1/} For optimal performance, connect leads 1 & 2 together (Anode).

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SH0022C

DOC



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ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop ^{2/} (I _F = 1 Adc, T _A = 25°C, 300 - 500µs Pulse) (I _F = 5 Adc, T _A = 25°C, 300 - 500µs Pulse) (I _F = 10 Adc, T _A = 25°C, 300 - 500µs Pulse)	V _{F1} V _{F2} V _{F3}	0.56 0.73 0.85	Vdc
Instantaneous Forward Voltage Drop (I _F = 5 Adc, T _A = -55°C, 300 - 500µs Pulse)	V _{F4}	0.82	Vdc
Reverse Leakage Current (Rated V _R , T _A = 25°C, 300µs Pulse Minimum)	I _{R1}	100	µA
Reverse Leakage Current (Rated V _R , T _A = 100°C, 300µs Pulse Minimum)	I _{R2}	5	mA
Junction Capacitance (V _R = 10 Vdc, T _A = 25°C, f = 1 MHz)	C _J	400	pF

NOTES:

^{2/} V_F as measured between pins 1 and 2 in common, within .100" from the case, and pin 3 directly at the case.

